



40V PNP MEDIUM POWER TRANSISTOR IN SOT89

Features

- BV_{CEO} > -40V
- I_C = -3.5A High Continuous Current
- Low Saturation Voltage V_{CE(sat)} < -90mV @ -1A
- $R_{sat} = 55m\Omega$ for a Low Equivalent On-Resistance
- Complementary part number: ZXTN25040DZ
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen- and Antimony-Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

Mechanical Data

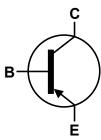
- Case: SOT89
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208
- Weight: 0.05 grams (Approximate)

Application

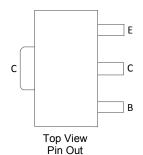
- MOSFET and IGBT gate driving
- DC DC converters
- Motor drive
- · High side driver



Top View



Device Symbol



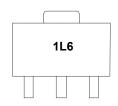
Ordering Information (Note 4)

ĺ	Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
	ZXTP25040DZTA	Standard	1L6	7	12	1,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



1L6 = Product Type Marking Code



Absolute Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-45	V
Collector-Emitter Voltage (forward blocking)	V _{CEO}	-40	V
Emitter-Collector voltage (reverse blocking)	V _{ECO}	-3	V
Emitter-Base Voltage	V _{EBO}	-7	V
Continuous Collector Current	Ic	-3	Α
Peak Pulse Collector Current (Single Pulse)	Ісм	-9	Α
Base current	I _B	-1	Α

Thermal Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5) Linear Derating Factor	PD	1.1 8.8	W mW/°C
Power Dissipation (Note 6) Linear Derating Factor	P _D	1.8 14.4	W mW/°C
Power Dissipation (Note 7) Linear Derating Factor	P _D	2.4 19.2	W mW/°C
Power Dissipation (Note 8) Linear Derating Factor	P _D	4.46 35.7	W mW/°C
Power Dissipation (Note 9) Linear Derating Factor	P _D	15.7 126	W mW/°C
Thermal Resistance, Junction to Ambient (Note 5)	ReJA	117	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	ReJA	68	°C/W
Thermal Resistance, Junction to Ambient (Note 7)	ReJA	51	°C/W
Thermal Resistance, Junction to Ambient (Note 8)	$R_{\theta JA}$	28	°C/W
Thermal Resistance, Junction to Case (Note 9)	R _{eJC}	7.95	°C/W
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	°C

Notes:

^{5.} For a device surface mounted on 15mm x 15mm x 0.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; device measured when operating in steady state condition.

6. Same as note (5), except the device is mounted on 25mm x 25mm x 0.6mm single sided 1oz weight copper.

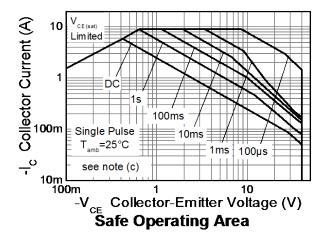
7. Same as note (5), except the device is mounted on 50mm x 50mm x 0.6mm single sided 1oz weight copper.

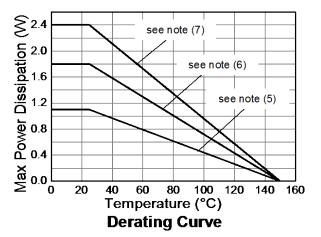
8. Same as note (5), except the device is measured at t<5 seconds

^{9.} Junction to case (collector tab). Typical.



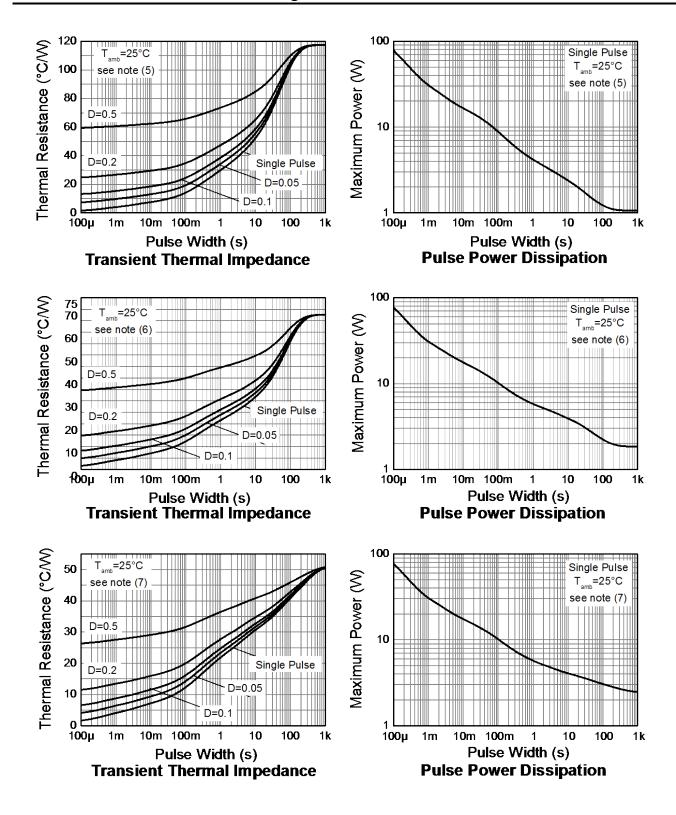
Thermal Characteristics and Derating Information







Thermal Characteristics and Derating Information





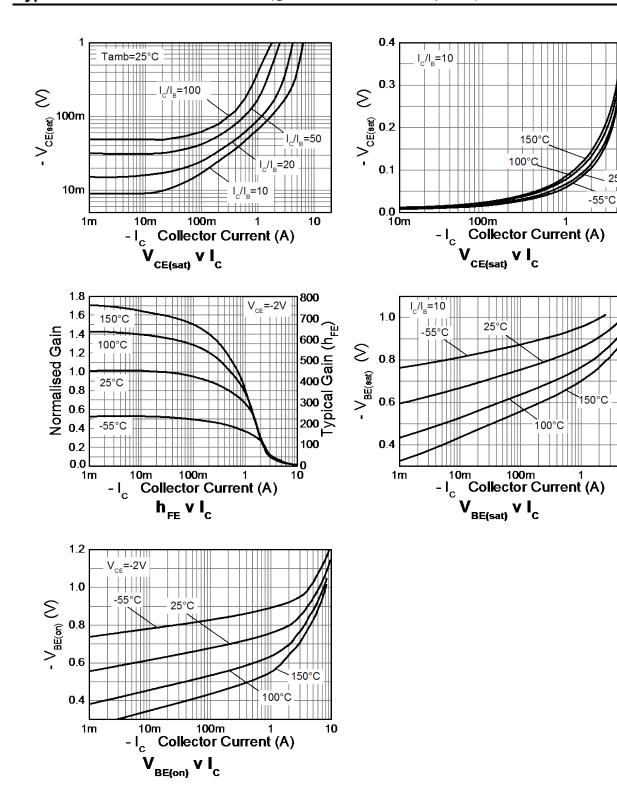
Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_CBO	-45	-75	_	V	I _C = -100μA
Collector-Emitter Breakdown Voltage (Note 10)	BV_CEO	-40	-65	_	V	I _C = -10mA
Emitter-Collector Breakdown Voltage	BV _{ECO}	-3	-8.7	_	V	I _E = -100μA
Emitter-Base Breakdown Voltage	BV_{EBO}	-7	-8.2	_	V	I _E = -100μA
Collector Cut-Off Current	I _{CBO}	_	-1 —	-50 -0.5	nA μA	V _{CB} = -45V V _{CB} = -45V, T _A = +100°C
Emitter Cut-Off Current	I _{EBO}	_	-1	-50	nA	V _{EB} = -5.6V
Collector-Emitter Saturation Voltage (Note 10)	$V_{\text{CE}(\text{sat})}$	_	-170 -70 -215	-265 -90 -350	mV	$I_C = -1A$, $I_B = -20mA$ $I_C = -1A$, $I_B = -100mA$ $I_C = -3.5A$, $I_B = -350mA$
Base-Emitter Saturation Voltage (Note 10)	V _{BE(sat)}	_	-970	-1050	mV	I _C = -3.5A, I _B = -350mA
Base-Emitter Turn-On Voltage (Note 10)	V _{BE(on)}	_	-870	-950	mV	I _C = -3.5A, V _{CE} = -2V
DC Current Gain (Note 10)	h _{FE}	300 200 20	450 300 50	900 — —	_	I _C = -10mA, V _{CE} = -2V I _C = -1A, V _{CE} = -2V I _C = -3.5A, V _{CE} = -2V
Transitional frequency	f _T	_	270	_	MHz	$I_C = -50$ mA, $V_{CE} = -10$ V, $f = 100$ MHz
Input Capacitance	C _{ibo}	_	142	_	pF	V _{EB} = -0.5V, f = 1MHz
Output Capacitance	C_{obo}	_	17.4	_	pF	V _{CB} = -10V, f = 1MHz
Switching Time	t _{on} t _{off}	_	75.5 320	_	ns	$V_{CC} = -15V$, $I_C = -750$ mA, $I_{B1} = -I_{B2} = -15$ mA

Note: 10. Measured under pulsed conditions. Pulse width \leqslant 300 $\mu s.$ Duty cycle \leqslant 2%.



Typical Electrical Characteristics (@ TA = +25°C, unless otherwise specified.)



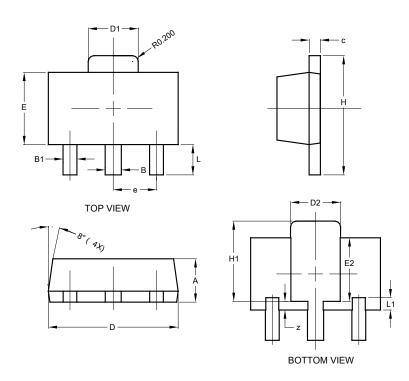
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Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT89

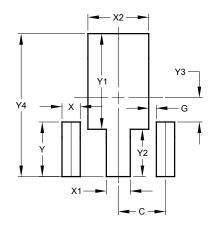


SOT89					
Dim	Min	Max	Тур		
Α	1.40	1.60	1.50		
В	0.50	0.62	0.56		
B1	0.42	0.54	0.48		
С	0.35	0.43	0.38		
D	4.40	4.60	4.50		
D1	1.62	1.83	1.733		
D2	1.61	1.81	1.71		
Е	2.40	2.60	2.50		
E2	2.05	2.35	2.20		
е	-	-	1.50		
Н	3.95	4.25	4.10		
H1	2.63	2.93	2.78		
L	0.90	1.20	1.05		
L1	0.327	0.527	0.427		
Z	0.20	0.40	0.30		
All	All Dimensions in mm				

Suggested Pad Layout

 $\label{prop:lease} Please see \ http://www.diodes.com/package-outlines.html \ for \ the \ latest \ version.$

SOT89



Dimensions	Value (in mm)	
С	1.500	
G	0.244	
X	0.580	
X1	0.760	
X2	1.933	
Y	1.730	
Y1	3.030	
Y2	1.500	
Y3	0.770	
Y4	4.530	



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